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(54) **Title: PROCESSING SYSTEM AND METHODS FOR FORMING VOID-FREE AND SEAM-FREE TUNGSTEN FEATURES**

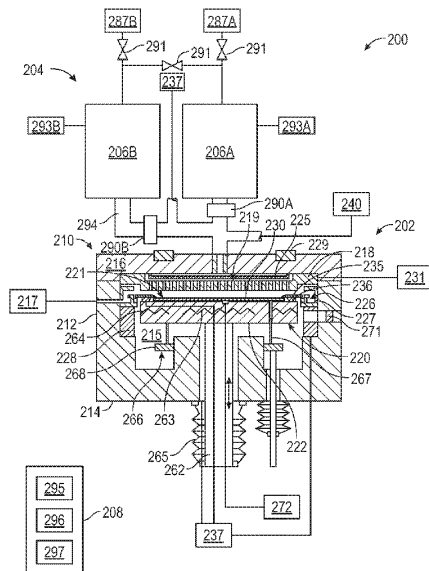


FIG. 2A

(57) **Abstract:** Embodiments herein are generally directed to electronic de-
vice manufacturing and, more particularly, to systems and methods for form-
ing substantially void-free and seam-free tungsten features in a semiconduc-
tor device manufacturing scheme. In one embodiment, a substrate process-
ing system features a processing chamber and a gas delivery system fluidly
coupled to the processing chamber. The gas delivery system includes a first
radical generator for use in a differential inhibition treatment process and a
second radical generator for use in a chamber clean process.

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